## **Comments and Corrections**

## Corrections to "CW Gain Characteristics of Linear Optical Amplifiers"

W. Zheng and G. W. Taylor

In the above paper [1, Sec. II, p. 715], equation (3) was left out of the final printing. The text should have read as follows:

The stimulated lifetime  $\tau_{sti}$  has been derived as [7]



Fig. 4. Log plot of the distribution of the LOA photon density along the amplifier's cavity at I = 150 mA and various signal power for a single-wavelength input  $\lambda = 1540$  nm. (Dashed lines represent direct solutions in Region I; Stars represent numerical solutions and solid lines represent analytical solutions in Region II. This is same in Figs. 5 and 6).



where  $D_n$  and  $D_p$  are the electron and hole densities of states, respectively,  $\bar{B}$  is the modified Einstein coefficient and  $h\bar{\nu}_i = h\nu_i - (E_g + E_{1p} + E_{1n})$  is the energy difference between laser output and QW bandgap between first subband energies of electrons and holes.

Also, in Fig. 4–6, the horizontal position should be in centimeters instead of microns. The corrected figures are printed.

## REFERENCES

 W. Zheng and G. W. Taylor, "CW Gain Characteristics of Linear Optical Amplifiers," *IEEE J. Quantum Electron.*, vol. 43, no. 8, pp. 714–721, Aug. 2007.

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Fig. 5. Log plot of the distribution of the VCSEL photon density along the amplifier's cavity at I = 150 mA and various signal power for a single-wavelength input  $\lambda = 1540$  nm.



Fig. 6. Electron density profile at I = 150 mA and various signal power for a single-wavelength input  $\lambda = 1540$  nm.